

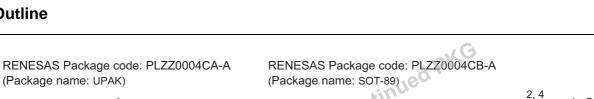
Thyristor Low Power Use

REJ03G0348-0300 Rev.3.00 Mar 22, 2007

Features

- $I_{T(AV)}: 0.5 A$
- V_{DRM} : 400 V •
- I_{GT} : 100 μA •

Outline



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Non-Insulated Type

Planar Passivation Type



to be di

1. Cathode 2. Anode 3. Gate 4. Anode

Applications

Solid state relay, strobe flasher, igniter, and hybrid IC

Maximum Ratings

(Package name: UPAK)

Parameter	Symbol	Voltage class	Unit	
	Symbol	8 (Mark CD)	Onic	
Repetitive peak reverse voltage	V _{RRM}	400	V	
Non-repetitive peak reverse voltage	V _{RSM}	500	V	
DC reverse voltage	V _{R (DC)}	320	V	
Repetitive peak off-state voltage ^{Note1}	V _{DRM}	400	V	
DC off-state voltage ^{Note1}	V _{D (DC)}	320	V	

查询"CRAMeter 供应商	Symbol	Ratings	Unit	Conditions
RMS on-state current	I _{T (RMS)}	0.79	А	
Average on-state current	I _{T (AV)}	0.5	A	Commercial frequency, sine half wave 180° conduction, Ta = $57^{\circ}C^{Note2}$
Surge on-state current	I _{TSM}	10	A	60Hz sine half wave 1 full cycle, peak value, non-repetitive
l ² t for fusing	l ² t	0.4	A ² s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P _{GM}	0.1	W	
Average gate power dissipation	P _{G (AV)}	0.01	W	
Peak gate forward voltage	V _{FGM}	6	V	
Peak gate reverse voltage	V _{RGM}	6	V	
Peak gate forward current	I _{FGM}	0.1	A	
Junction temperature	Tj	- 40 to +125	°C	
Storage temperature	Tstg	- 40 to +125	°C	
Mass	—	50	mg	Typical value

Notes: 1. With gate to cathode resistance $R_{GK} = 1 \ k\Omega$.

Electrical Characteristics

Parameter	Symbol	Rated value			11	Test conditions
		Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak reverse current	I _{RRM}	—	—	0.1	mA	Tj = 125°C, V _{RRM} applied
Repetitive peak off-state current	I _{DRM}		—	0.1	mA	Tj = 125°C, V _{DRM} applied, R _{GK} = 1 k Ω
On-state voltage	V _{TM}		—	1.9	V	Ta = 25°C, I_{TM} = 1.5 A, instantaneous value
Gate trigger voltage	V _{GT}		—	0.8	V	$\label{eq:transform} \begin{split} Tj &= 25^\circ C, \ V_D = 6 \ V, \\ I_T &= 0.1 \ A^{Note4} \end{split}$
Gate non-trigger voltage	V_{GD}	0.2	—	_	V	$\label{eq:Tj} \begin{split} Tj &= 125^\circ C, \ V_D = 1/2 \ V_{DRM}, \\ R_{GK} &= 1 \ k\Omega \end{split}$
Gate trigger current	I _{GT}	20	—	100 ^{Note3}	μA	$\label{eq:transform} \begin{split} Tj &= 25^\circ C, \ V_D = 6 \ V, \\ I_T &= 0.1 \ A^{Note4} \end{split}$
Holding current	I _H	—	—	3	mA	$\label{eq:transform} \begin{array}{l} Tj=25^{\circ}C,V_{D}=12~V,\\ R_{GK}=1~k\Omega \end{array}$
Thermal resistance	R _{th (j-a)}	_	—	70	°C/W	Junction to ambient ^{Note2}

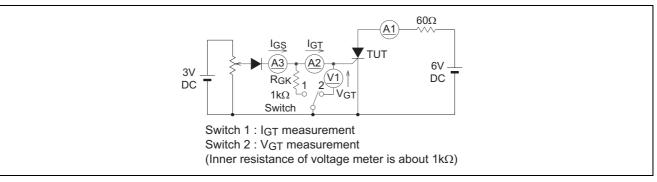
Notes: 2. Soldering with ceramic plate (25 mm \times 25 mm \times t0.7 mm).

3. If special values of I_{GT} are required, choose item E from those listed in the table below if possible.

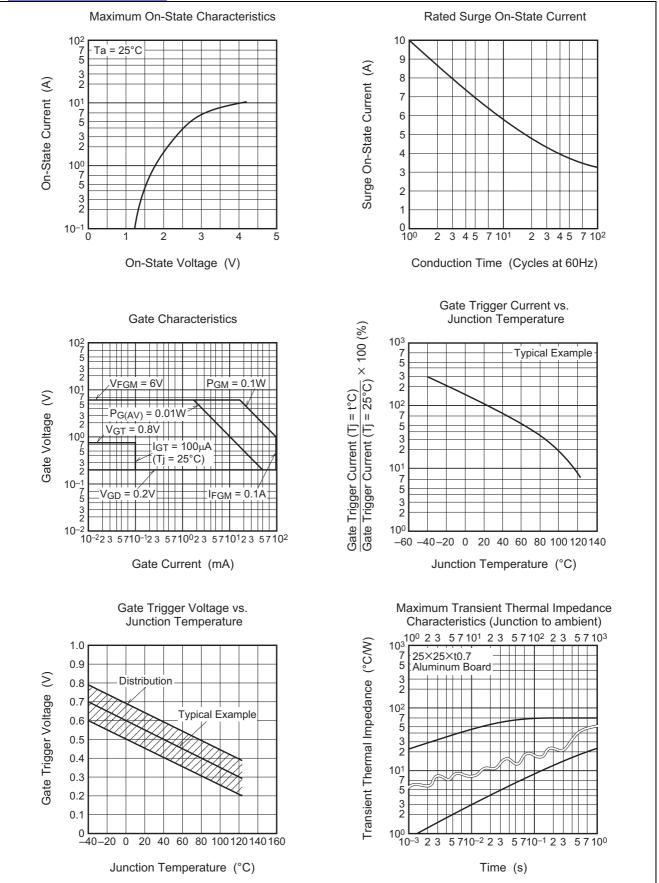
ltem	В	E	
I _{GT} (μA)	20 to 50	20 to 100	

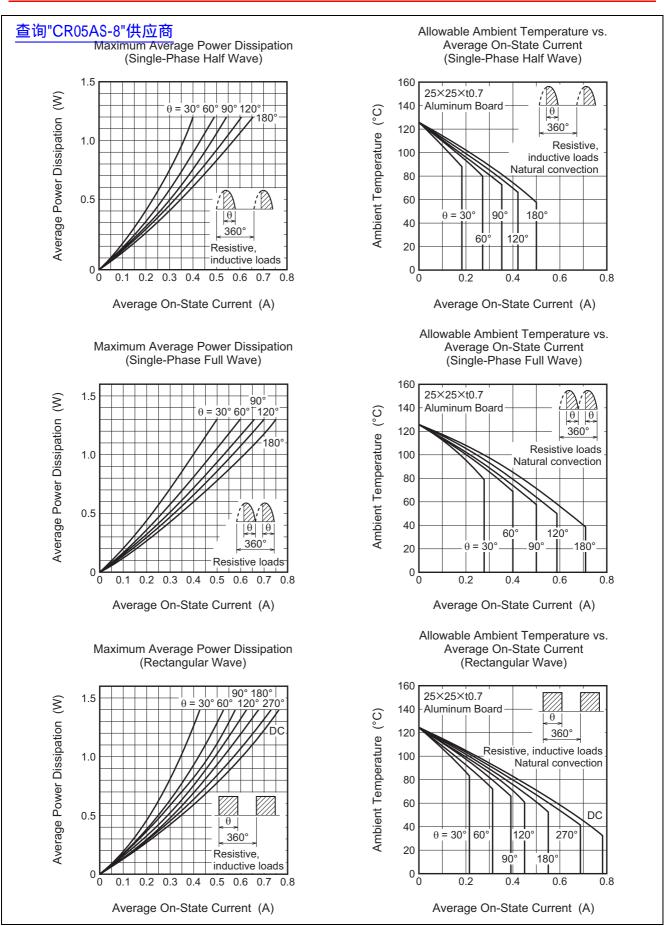
The above values do not include the current flowing through the 1 $k\Omega$ resistance between the gate and cathode.

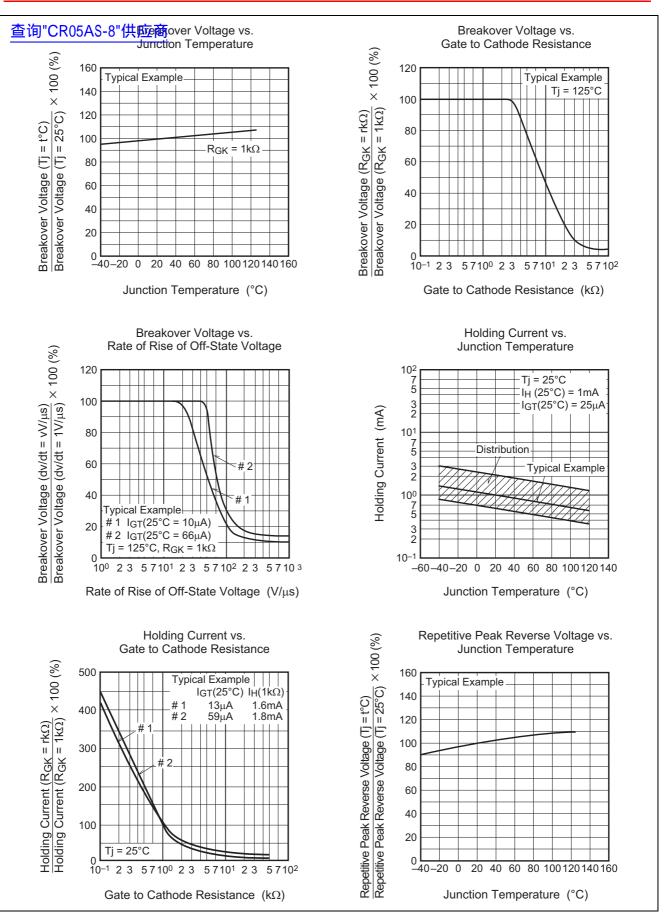
4. I_{GT}, V_{GT} measurement circuit.

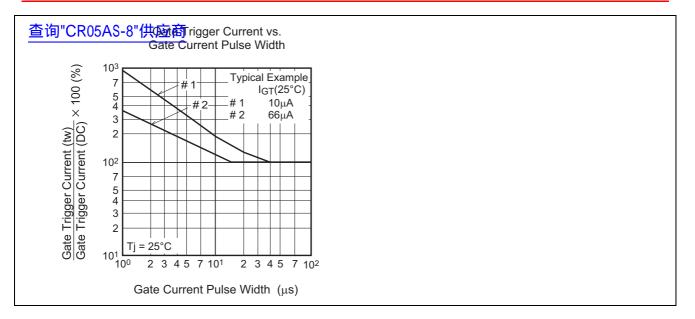


Parformance Surves

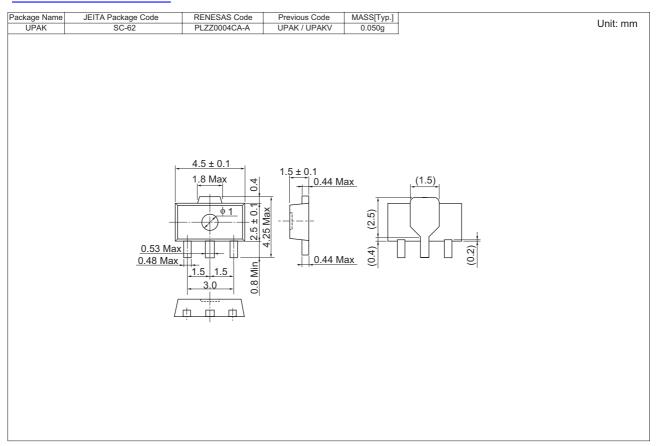


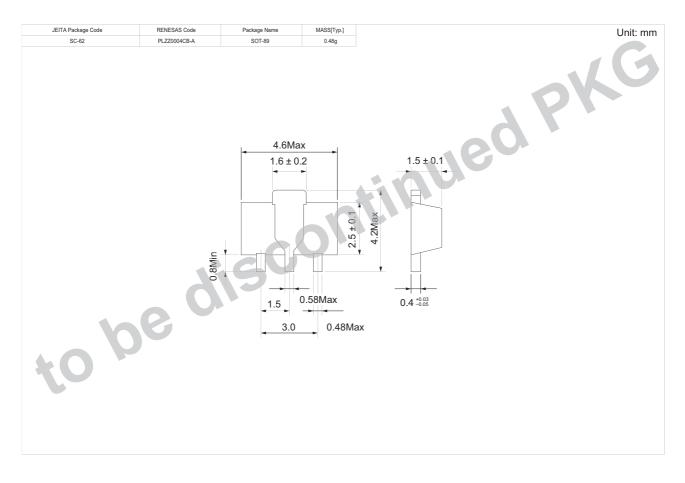






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CR05AS-8

Order Code CR05AS-8"供应商

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	4000	Type name – ET +Direction (1 or 2) + 4	CR05AS-8-ET14

Note : Please confirm the specification about the shipping in detail.

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Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510

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